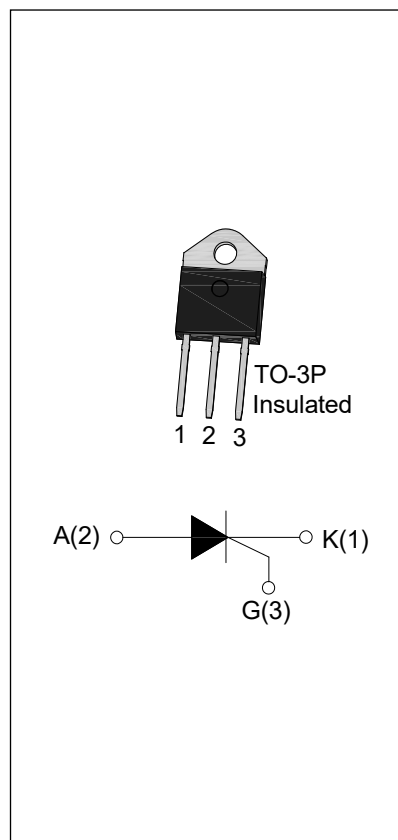




DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT1240Z provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT1240Z provides a rated insulation voltage of 2500 V_{RMS}, complying with UL standards (File ref: E252906).Package TO-3P is RoHS compliant. (2011/65/EU)



MAIN FEATURES

Symbol	Value	Unit
V _{DRM} / V _{R_{RRM}}	1200	V
I _{T(RMS)}	40	A
I _{GT}	≤45	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T _{stg}	-40-150	°C
Operating junction temperature range	T _j	-40-125	°C
Repetitive peak off-state voltage(T _j =25°C)	V _{DRM}	1200	V
Repetitive peak reverse voltage(T _j =25°C)	V _{R_{RRM}}	1200	V
RMS on-state current	I _{T(RMS)}	40	A
	TO-3P(Ins) (T _C =90°C)		
Non repetitive surge peak on-state current (tp=10ms)	I _{TSM}	400	A
I ² t value for fusing (tp=10ms)	I ² t	800	A ² s
Critical rate of rise of on-state current (I _G =2×I _{GT})	dI/dt	150	A/μs
Peak gate current	I _{GM}	4	A

Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}C$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V R_L=33\Omega$	-	15	45	mA
V_{GT}		-	-	1.5	V
V_{GD}	$V_D=V_{DRM} T_j=125^{\circ}C R_L=3.3K\Omega$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	150	mA
I_H	$I_T=500mA$	-	-	100	mA
dv/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^{\circ}C$	1000	-	-	V/ μs

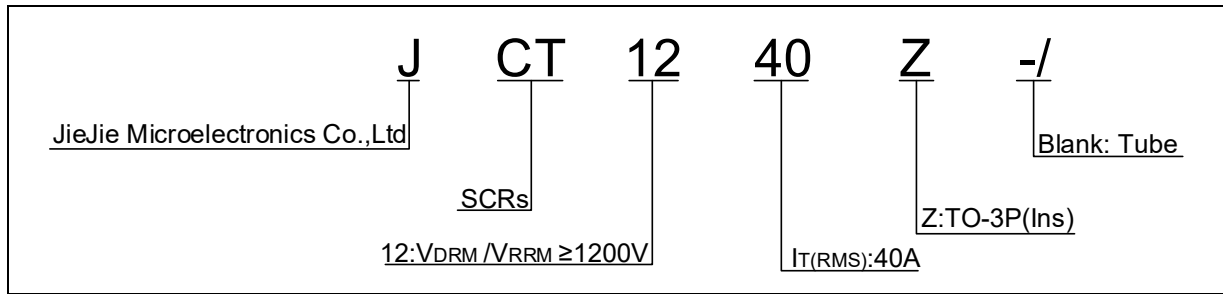
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=80A t_p=380\mu s$	$T_j=25^{\circ}C$	1.6	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}C$	10	μA
I_{RRM}		$T_j=125^{\circ}C$	4	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-3P(Ins)	1.1	$^{\circ}C/W$

ORDERING INFORMATION



ORDERING INFORMATION

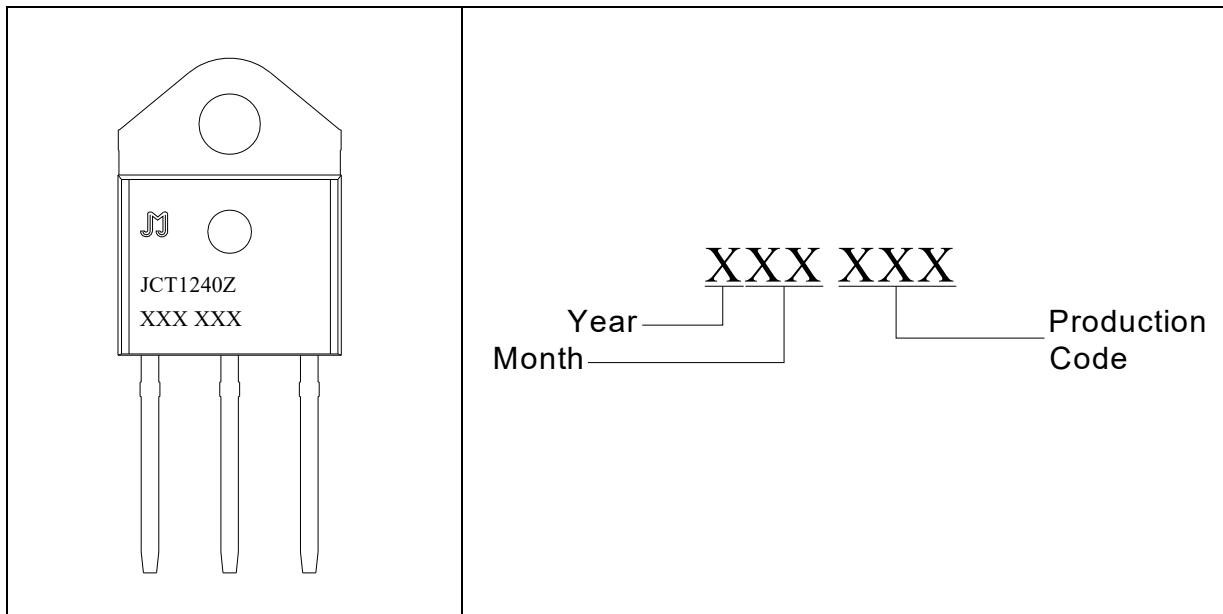


FIG.1 Maximum power dissipation versus RMS on-state current

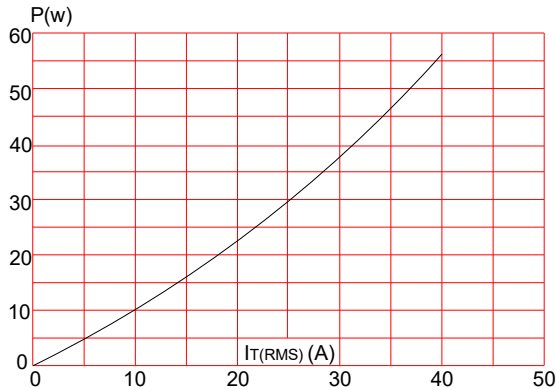


FIG.3: Surge peak on-state current versus number of cycles

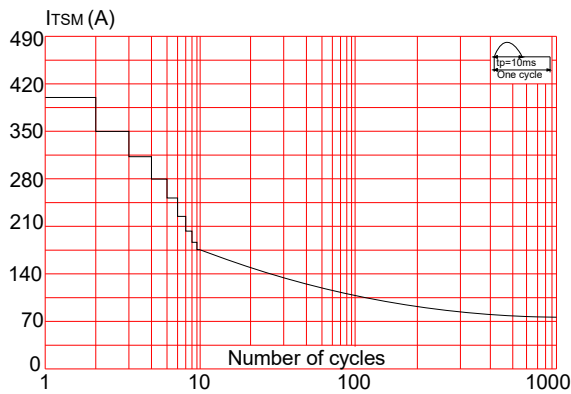


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 150\text{A}/\mu\text{s}$)

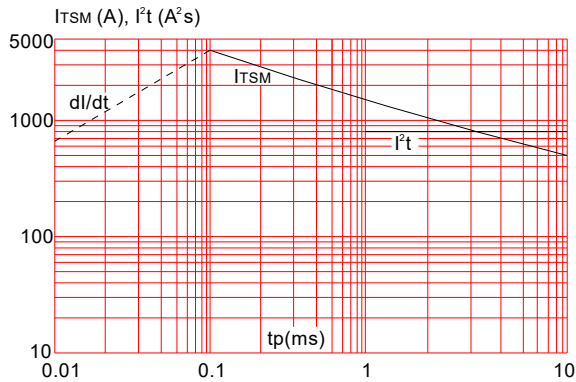


FIG.2: RMS on-state current versus case temperature

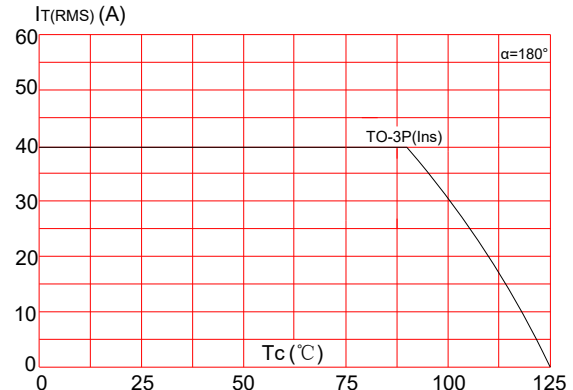


FIG.4: On-state characteristics (maximum values)

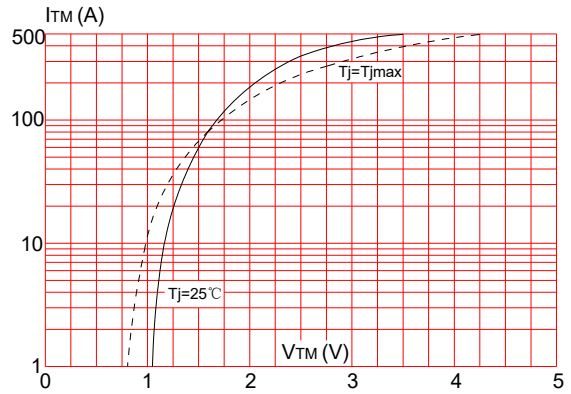
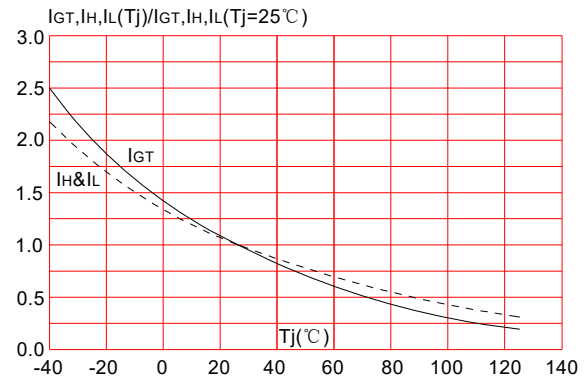


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



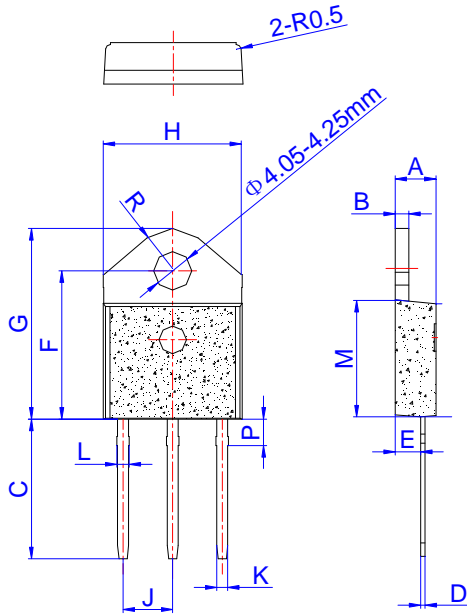
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT1240Z	1200	45	TO-3P(Ins)	30	Tube

Document Revision History

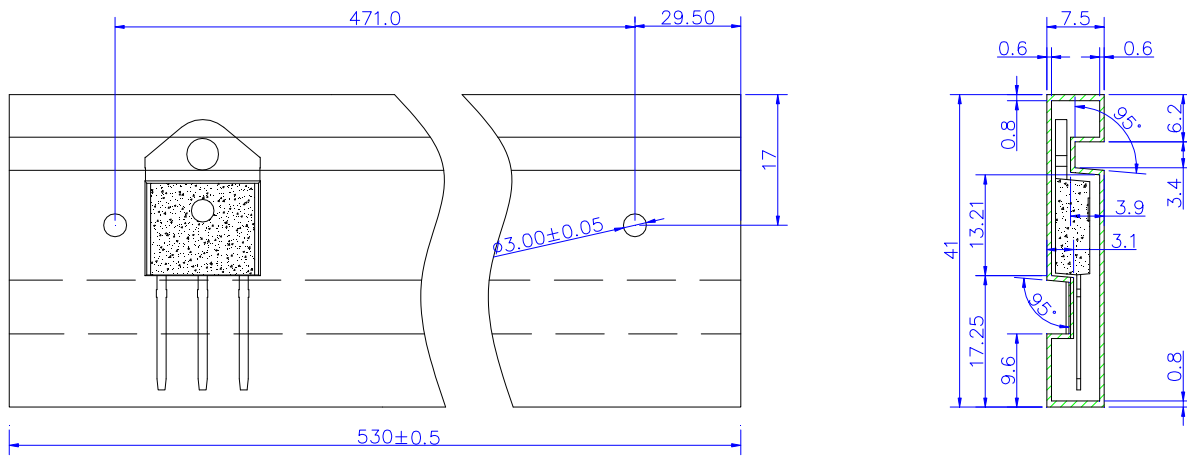
Date	Revision	Changes
Mar 17, 2022	1	Last update

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.50		0.70	0.020		0.028
E	2.70		2.90	0.106		0.114
F	15.80		16.50	0.622		0.650
G	20.40		21.10	0.803		0.831
H	15.10		15.50	0.594		0.610
J	5.40		5.65	0.213		0.222
K	1.10		1.40	0.043		0.055
L	1.25		1.45	0.049		0.057
M	12.37		12.77	0.487		0.503
P	2.80		3.00	0.110		0.118
R		4.35			0.171	


DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-3P	TUBE	30	450	2,250



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